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U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	1	of	12	Attorney Docket Number	0756-7218

10/7/2,062

U.S. PATENT DOCUMENTS						
Examiner Initials ²	Cite No. ¹	U.S. Patent Document		Name of Patent or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ³ (if known)			
Pr		5,686,328		Zhang et al.	11/11/97	
		5,763,899		Yamazaki et al.	06/09/98	
		5,782,665		Weisfield et al.	07/21/98	
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M		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.	
N		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995	

Examiner Signature		Date Considered	8/23/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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PR		5,811,327		Funai et al.	09/22/98	
		5,818,076		Zhang et al.	10/06/98	
		5,821,138		Yamazaki et al.	10/13/98	
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		JP	07-335900	Teramoto Satoshi	12/22/95	Abst.
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PR		IBM Technical Disclosure Bulletin, Vol. 11, No.7, A.R. Baker, Jr.	

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	2/8/05
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B		4,546,376		Nakata et al.	10/08/85
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PA		5,470,763		Hamada	11/28/95
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Sheet	8	of	12	Attorney Docket Number	0756-7218

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Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
7/8		Thompson et al., "Silicide Formation in Pd-a-Si:H Schottky Barriers," August 1981, pp. 274-276, Appl. Phys. Lett., Vol. 39, No. 3	
		Nemanich et al., "Initial Phase Formation at the Interface of Ni, Pd, or Pt and Si," 1984, pp. unknown, Mat. Res. Soc. Symp. Proc., Vol. 25	
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		Hemple et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Film," 1993, pp. 921-924, Solid State Communications, Vol. 85, No. 11	
		Kuo, "Thin Film Transistor Technologies," Vol. 94-35, pp. 116-122, The Electrochemical Society Proceedings	
		Author Unknown, "Thermo Auto-Chrome Full Color Recording Technology," May 31, 1995, pp. Unknown, Technology Information Association	
		Wolf et al., "Thermal Oxidation of Single Crystal Silicon," 1986, pp. 207-211, Silicon Processing for the VLSI Era	
		Erokhin et al., "Spatially Confined Nickel Disilicide Formation at 400C on Ion Implantation Preamorphized Silicon," Dec. 6, 1993, pp. 3173-3175, Appl. Phys. Lett. 63 (23)	
		Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR	
		Batstone et al., "Microscopic Processes in Crystallization," January 1, 1994, pp. 257-268, Solid State Phenomena, Vol. 37-38	
		Cammarata et al., "Silicide Precipitation and Silicon Crystallization in Nickel Implanted Amorphous Silicon Thin Films," Oct 10, 1990, pp. 2133-2138, J. Mater. Res. Vol. 5, No. 10	
		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," May 15, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)	

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	2/8/05
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	9	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. ¹	U.S. Patent Document		Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ¹ (if known)		
JS		5,705,829		01/06/98	
		5,712,191		01/27/98	
		5,756,364		05/26/98	
		5,619,044		04/08/97	
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		5,550,070		08/27/96	
		5,693,959		12/02/97	

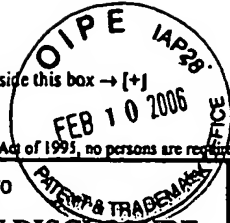
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NJZ		Kuznetsov et al., "Silicide Precipitate Formation and Solid Phase Re-Growth of Ni-Implanted Amorphous Silicon," April 5-8, 1993, pp. 191-194, Inst. Phys. Conf. Ser. No. 134.4: Proceedings of Royal Microscopical Society Conf.	
W		Liu et al., "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing," May 17, 1993, pp. 2554-2556, Appl. Phys. Lett 62(20)	
W		Liu et al., "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing," August 14, 1989, pp. 660-662, Appl. Phys. Lett 55(7)	
W		Spaepen et al., Metal-Enhanced Growth of Silicon, 1992, pp. 483-499, Crucial Issues in Semiconductor Materials & Processing Technologies	

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		First Named Inventor	Shunpei YAMAZAKI, et al.
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		Attorney Docket Number	0756-7218
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U.S. PATENT DOCUMENTS					
Examiner Initials ^a	Cite No. ^a	U.S. Patent Document		Name of Patent or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ^b (if known)		
[Signature]		5,403,772		Zhang et al.	04/04/95
		5,426,064		Zhang et al.	06/20/95
		5,481,121		Zhang et al.	01/02/96
		5,488,000		Zhang et al.	01/30/96
		5,492,843		Adachi et al.	02/20/96
		5,501,989		Takayama et al.	03/26/96
		5,508,533		Takemura	04/16/96
		5,529,937		Zhang et al.	06/25/96
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		5,543,352		Ohtani et al.	08/06/96
		5,563,426		Zhang et al.	10/08/96
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		5,569,936		Zhang et al.	10/29/96
		5,580,792		Zhang et al.	12/03/96
		5,585,291		Ohtani et al.	12/17/96
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		5,595,923		Zhang et al.	01/21/97
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		5,604,360		Zhang et al.	02/18/97
		5,605,846		Ohtani et al.	02/25/97
		5,606,179		Yamazaki et al.	02/25/97
		5,608,232		Yamazaki et al.	03/04/97
		5,612,250		Ohtani et al.	03/18/97
		5,614,426		Funada et al.	03/25/97
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		5,643,826		Ohtani et al.	07/01/97
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		5,677,549		Takayama et al.	10/14/97
		5,696,386		Yamazaki	12/09/97
		5,696,388		Funada et al.	12/09/97
		5,700,333		Yamazaki et al.	12/23/97

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				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet 11	of 12	Attorney Docket Number		0756-7218	

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		Number	Kind Code ² (if known)		
PK		5,932,893		Miyanaga et al.	08/03/99
		4,759,610		Yanagisawa	07/26/88
		5,535,471		Guldi	07/16/96
		5,661,056		Takeuchi	08/26/97
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		5,210,050		Yamazaki et al.	05/11/93
		5,298,075		Lagendijk et al.	03/29/94
		5,306,651		Masumo et al.	04/26/94
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		6,011,275		Ohtani et al.	01/04/00
		6,133,073		Yamazaki et al.	10/17/00

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PK		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990).	

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	2/8/05
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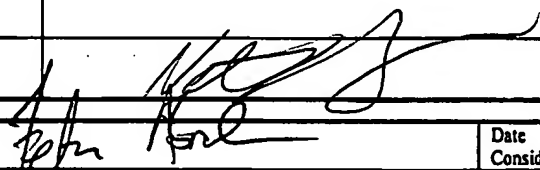
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				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	12	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
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		Number	Kind Code ² (if known)			
PR		6,225,152	B1	Yamazaki et al.	05/01/01	
		6,288,412	B1	Hamada et al.	09/11/01	
		6,323,072	B1	Yamazaki et al.	11/27/01	
		6,331,718	B1	Yamazaki et al.	12/18/01	

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		Office ⁴	Number ⁴				
NSR		JP	06-314785		11/08/94		Ab
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) MAR 27 2008 U.S. PATENT AND TRADEMARK OFFICE		Application Number	10/712,062
		Filing Date	November 14, 2003
		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2826
		Examiner Name	Fetsum Abraham
		Attorney Docket Number	0756-7218
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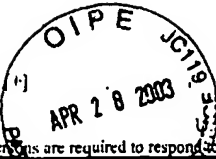
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NJA		Office Action dated August 3, 1998 for Application Serial No. 08/784,293.	
MEJ		Office Action dated February 11, 1999 for Application No. 08/784,293.	
MS		Office Action dated January 17, 2003 for Application No. 08/784,293.	
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		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2826
		Examiner Name	F. Abraham
		Attorney Docket Number	0756-7026
Sheet	1	of	1

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WZ		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990)	

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		Filing Date		November 14, 2003	
		First Named Inventor		Shunpei YAMAZAKI et al.	
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Sheet	1	of	1	Attorney Docket Number	0756-7218

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